## DESCRIPTION

The MGF2445A, power GaAs FET with an N-channel schottky gate, is designed for use in S to Ku band amplifiers.

# **FEATURES**

· High output power

P1dB = 32dBmW(TYP.) @f=12GHz

· High linear power gain

GLP = 6.0dB(TYP)

@f=12GHz

## APPLICATION

S to Ku band power amplifiers

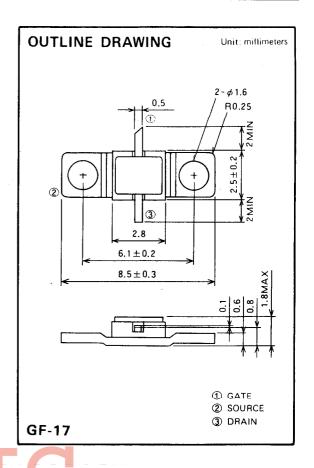
# QUALITY GRADE

## RECOMMENDED BIAS CONDITIONS

V<sub>DS</sub>=10V , I<sub>D</sub>=450mA

Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them . Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs , with appropriate measures such as (I) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
$V_{GDO}$	Gate to drain voltage	-15	V
V <sub>GSO</sub>	Gate to source voltage	-15	V
l <sub>D</sub>	Drain current 1500		mA
Igr	Reverse gate current	-3.6	mA
lgF	Forward gate current	15	mA
PT	Total power dissipation	10.0	W
T <sub>ch</sub>	T <sub>ch</sub> Channel temperature		ొ
T <sub>stg</sub>	Storage temperature	-65∼+175	ာ

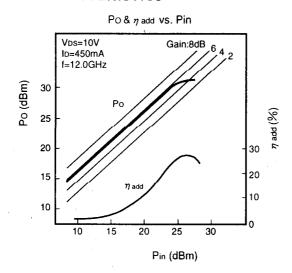
**ELECTRICAL CHARACTERISTICS** (Ta=25°C)

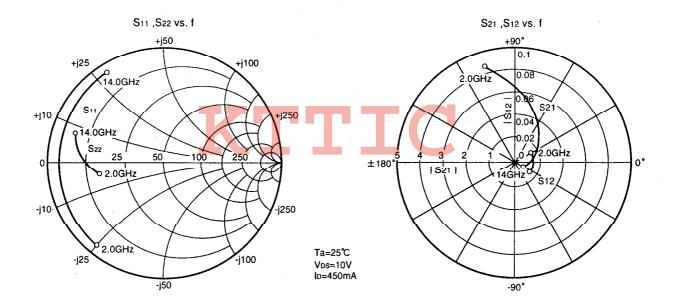
Symbol	Parameter	Test conditions	Limits			Unit
			MIN.	TYP.	MAX.	]
DSS	Saturated drain current	V <sub>DS</sub> =3V,VG=0V			1500	mA
gm	Transconductance	V <sub>DS</sub> =0V,I <sub>D</sub> =450mA		400		mS
V <sub>GS(off)</sub>	Gate to source cut-off voltage	V <sub>DS</sub> =3V,I <sub>D</sub> =3mA			-4.5	٧
P1dB	Output power at 1dB gain compression	V <sub>DS</sub> =10V,l <sub>D</sub> =450mA	31	32		dBm
GLP	Linear power gain	f=12GHz	5.5	6.0		dB
$\eta$ add	Power added efficiency			20		%
Rth(ch-c)	Thermal resistance	$\Delta$ Vf method			15	°C/W

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June/2004

# TYPICAL CHARACTERISTICS (Ta=25°C)





# S PARAMETERS ( $T_a = 25^{\circ}C$ , $V_{DS} = 10V$ , $I_D = 450 \text{mA}$ )

f	S Parameters (TYP.)							
٠. [	S <sub>11</sub>		S21		S12		S22	
(GHz)	Mag.	Angle (deg.)	Mag.	Angle (deg.)	Mag.	Angle (deg.)	Mag.	Angle (deg.)
2.0	0.914	-127.4	4.336	103.4	0.011	21.9	0.589	-175.6
4.0	0.889	-167.6	2.292	71.7	0.012	0.2	0.634	-177.1
6.0	0.886	170.5	1.451	49.6	0.012	-12.4	0.682	-179.6
8.0	0.889	154.7	0.999	31.2	0.012	-22.3	0.729	176.7
10.0	0.895	141.8	0.721	14.9	0.011	-31.0	0.773	172.2
12.0	0.902	130.7	0.535	0.4	0.011	-38.8	0.811	167.3
14.0	0.910	121.1	0.406	-12.7	0.010	-45.9	0.843	162.2

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MITSUBISHI SEMICONDUCTOR <GaAs FET>

**MGF2445A** 

**MICROWAVE POWER GaAs FET** 

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